

2SD552

SILICON NPN TRIPLE DIFFUSED TYPE

HIGH POWER AMPLIFIER APPLICATIONS.
HIGH POWER SWITCHING APPLICATIONS.
DC-DC CONVERTER APPLICATIONS.
REGULATOR APPLICATIONS.

FEATURES:

- High Power Dissipation : $P_C=150W$ ($T_C=25^\circ C$)
- High Collector Current : $I_C=15A$
- High Voltage : $V_{CE0}=180V$
- Complementary to 2SB552.

MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	220	V
Collector-Emitter Voltage	V_{CE0}	180	V
Emitter-Base Voltage	V_{EB0}	5	V
Collector Current	I_C	15	A
Base Current	I_B	3	A
Collector Power Dissipation ($T_C=25^\circ C$)	P_C	150	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-65~150	$^\circ C$

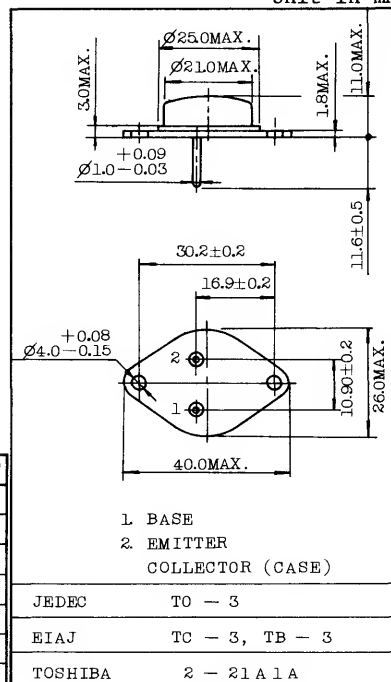
ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=150V, I_E=0$	-	-	100	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	1	mA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=50mA, I_B=0$	180	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=5V, I_C=5A$	25	-	80	
	$h_{FE(2)}$	$V_{CE}=5V, I_C=15A$	10	15	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10A, I_B=1A$	-	-	2.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-	1.5	2.5	V
Transition Frequency	f_T	$V_{CE}=10V, I_C=1A$	-	4	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=50V, I_E=0, f=1MHz$	-	160	-	pF
Switching Time	Turn-on Time		-	1	-	μs
	Storage Time		-	3.5	-	
	Fall Time		-	0.5	-	

Note : $h_{FE(1)}$ Classification BN : 25~50, R : 40~80

INDUSTRIAL APPLICATIONS

Unit in mm



Mounting Kit No. AC73

Weight : 12.9g

